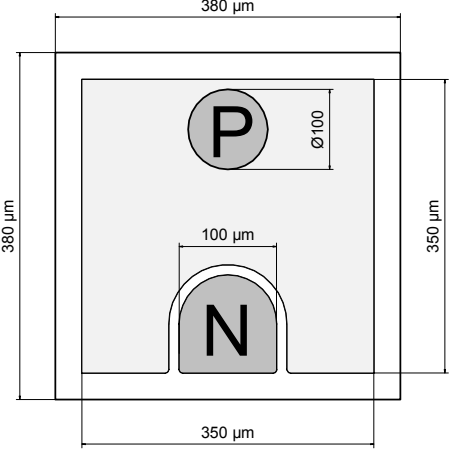


Radiation	Type	Technology	Electrodes
Green	Standard	InGaN/Al ₂ O ₃	Both on top side

	typ. dimensions in μm (±20 μm)	
	typ. thickness	90 (±20) μm
	front side metalization	Au-alloy, 0.5 μm
	backside metalization	Al-alloy, 1.5 μm

Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I _F	20	mA
Peak forward current	(t _p ≤ 50 μs, t _p /T = 1/2)	I _{FM}	100	mA
Operating temperature range		T _{amb}	-40 to +85	°C
Storage temperature range		T _{stg}	-40 to +100	°C

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		3.3	3.5	V
Reverse voltage	I _F = 1 μA	V _R	5			V
Luminous intensity ¹	I _F = 20 mA	I _v	220	280		mcd
Dominant wavelength	I _F = 20 mA	λ _D	480	490	500	nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		25		nm
Switching time	I _F = 20 mA	t _r , t _f		20		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	I _v (typ) [mcd]	V _F (typ) [V]	Quantity
ELC-490-37				

Packing: Chips on adhesive film with wire-bond side on top